

GM2907A

PNP EPITAXIAL PLANAR TRANSISTOR

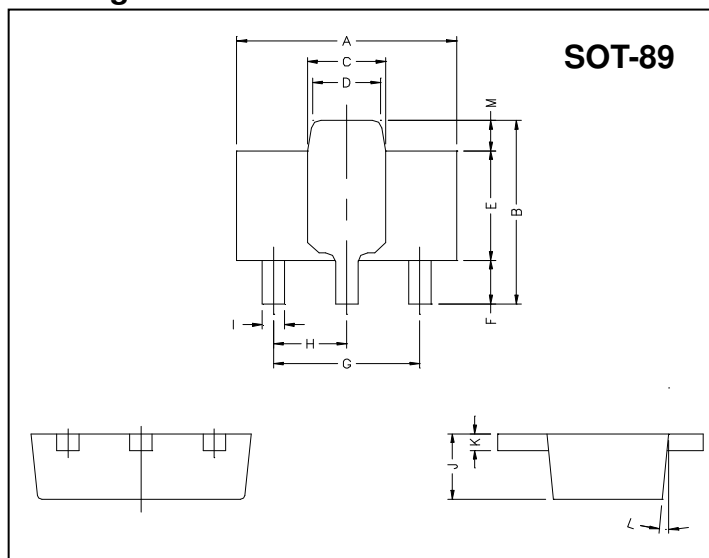
Description

The GM2907A is designed for general purpose amplifier and high speed switching, medium-power switching applications.

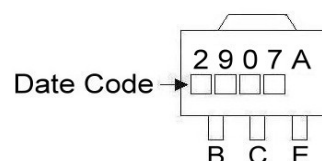
Features

- Low Collector Saturation Voltage
- High Speed Switching
- For Complementary Use With NPN Type GM2222A

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5°	TYP.
			M	0.70	REF.

Absolute Maximum Ratings at Ta = 25°C

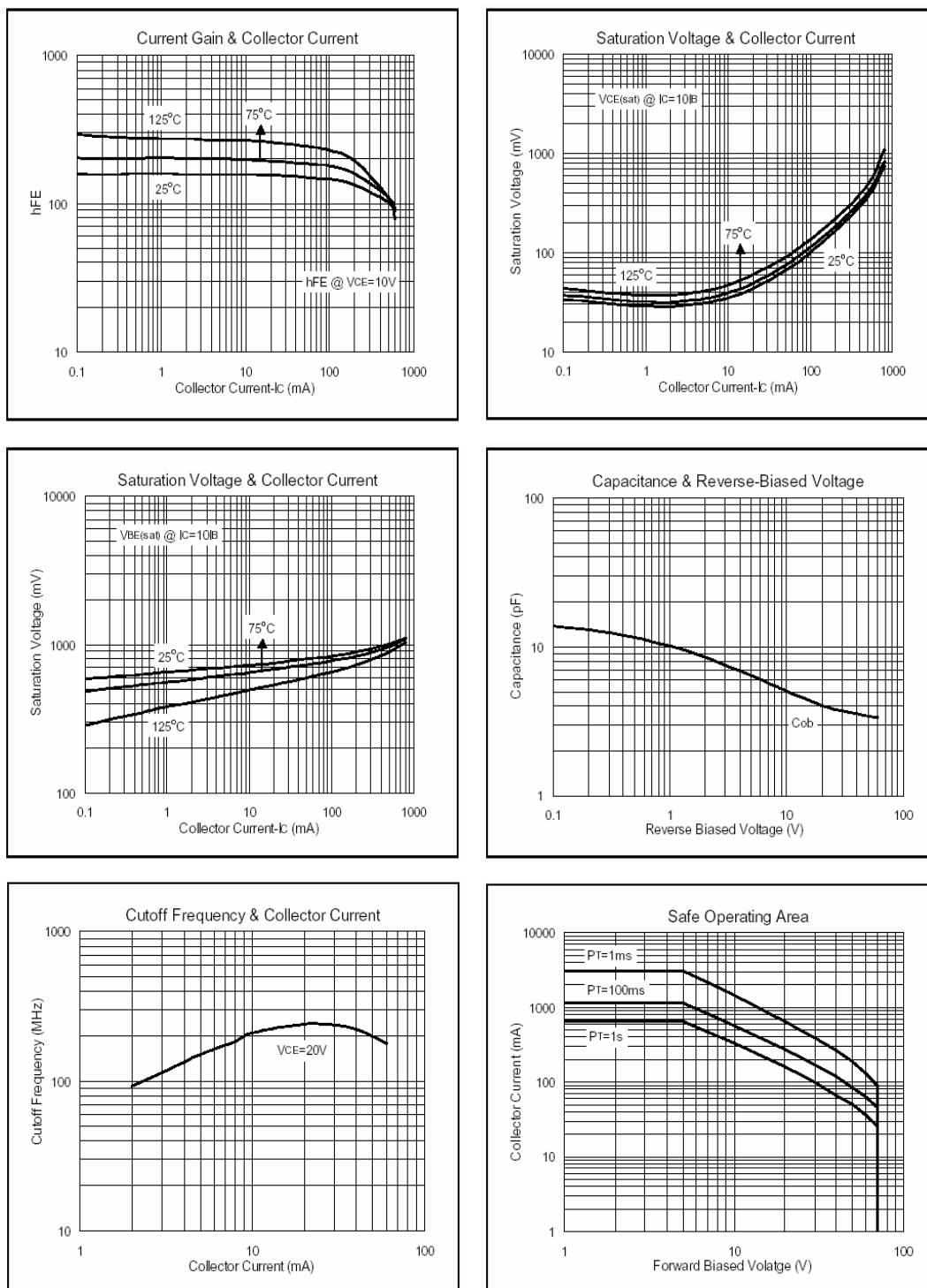
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	VCBO	-60	V
Collector to Emitter Voltage at Ta=25°C	VCEO	-60	V
Emitter to Base Voltage at Ta=25°C	VEBO	-5	V
Collector Current at Ta=25°C	IC	-600	mA
Total Power Dissipation at Ta=25°C	PD	1.2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-60	-	-	V	IC=-10uA
BVCEO	-60	-	-	V	IC=-10mA
BVEBO	-5	-	-	V	IE=-10uA
ICBO	-	-	-10	nA	VCE=-50V
ICEX	-	-	-50	nA	VCE=-30V, VBE=-0.5V
*VCE(sat)1	-	-0.2	-0.4	V	IC=-150mA, IB=-15mA
*VCE(sat)2	-	-0.5	-1.6	V	IC=-500mA, IB=-50mA
*VBE(sat)1	-	-	-1.3	mV	IC=-150mA, IB=-15mA
*VBE(sat)2	-	-	-2.6	V	IC=-500mA, IB=-50mA
*hFE1	75	-	-		VCE=-10V, IC=-0.1mA
*hFE2	100	-	-		VCE=-10V, IC=-1mA
*hFE3	100	-	-		VCE=-10V, IC=-10mA
*hFE4	100	-	300		VCE=-10V, IC=-150mA
*hFE5	50	-	-		VCE=-10V, IC=-500mA
fT	200	-	-	MHz	VCE=-20V, IC=-50mA, f=100MHz
Cob	-	-	8.0	pF	VCE=-10V, f=1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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